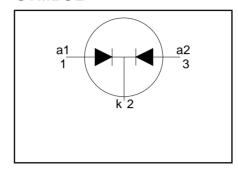
BYV32F, BYV32EX series

FEATURES

- Low forward volt drop
- Fast switching
- · Soft recovery characteristic
- Reverse surge capability
- High thermal cycling performance
- · Isolated mounting tab

SYMBOL



QUICK REFERENCE DATA

$$V_{R} = 150 \text{ V}/200 \text{ V}$$

$$V_{F} \le 0.85 \text{ V}$$

$$I_{O(AV)} = 12 \text{ A}$$

$$I_{RRM} = 0.2 \text{ A}$$

$$t_{rr} \le 25 \text{ ns}$$

GENERAL DESCRIPTION

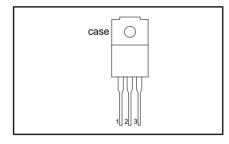
Dual, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV32F series is supplied in the SOT186 package. The BYV32EX series is supplied in the SOT186A package.

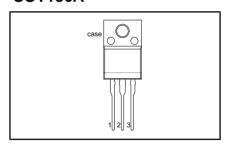
PINNING

| PIN | DESCRIPTION | | |
|-----|-------------|--|--|
| 1 | anode 1 (a) | | |
| 2 | cathode (k) | | |
| 3 | anode 2 (a) | | |
| tab | isolated | | |

SOT186



SOT186A



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | | UNIT |
|--|--|---|----------|----------------------------------|----------------------------------|----------|
| V _{RRM} V _{RWM} V _R | Peak repetitive reverse voltage Crest working reverse voltage Continuous reverse voltage | BYV32F / BYV32EX | | -150 150 150 150 | -200 200 200 200 | V V |
| I _{O(AV)} | Average rectified output current (both diodes conducting) ¹ | $\delta = 0.5$; $T_{hs} \le 95$ °C | - | 1 | 2 | A |
| I _{FRM} | Repetitive peak forward current per diode | $t = 25 \ \mu s; \ \delta = 0.5;$ $T_{hs} \le 95 \ ^{\circ}C$ | - | 2 | 0 | A |
| I _{FSM} | Non-repetitive peak forward current per diode | t = 10 ms t = 8.3 ms sinusoidal; with reapplied | - | | 25 37 | A A |
| I _{RRM} | Repetitive peak reverse current per diode | $V_{\text{RWM(max)}} $ $t_p = 2 \ \mu \text{s}; \ \delta = 0.001$ | - | 0 | .2 | A |
| I _{RSM} | Non-repetitive peak reverse current per diode | $t_{p} = 100 \ \mu s$ | - | 0 | .2 | Α |
| ${\mathsf T}_{stg} \atop {\mathsf T}_{\mathsf j}$ | Storage temperature Operating junction temperature | | -40 - | | 50 50 | °C °C |

¹ Neglecting switching and reverse current losses

BYV32F, BYV32EX series

ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|----------------|---|---|------|------|------|
| V _C | Electrostatic discharge capacitor voltage | Human body model; C = 250 pF; R = 1.5 kΩ | - | 8 | kV |

ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------|--|--|---------|------|------|------|
| STIVIBUL | PARAIVIETER | CONDITIONS | IVIIIN. | ITP. | WAA. | UNII |
| V _{isol} | R.M.S. isolation voltage from all three terminals to external heatsink | SOT186A package; f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree | 1 | | 2500 | > |
| V _{isol} | Repetitive peak voltage from all three terminals to external heatsink | SOT186 package; R.H. ≤ 65%; clean and dustfree | - | | 1500 | V |
| C _{isol} | Capacitance from pin 2 to external heatsink | f = 1 MHz | - | 10 | - | pF |

THERMAL RESISTANCES

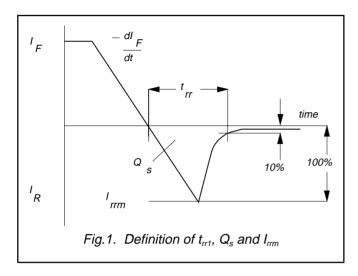
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------------|----------------------|--|------|--------------|-----------------|-------------------|
| R _{th j-hs} | heatsink (per diode) | with heatsink compound without heatsink compound in free air | | - - 55 | 5.0 7.0 - | K/W K/W K/W |

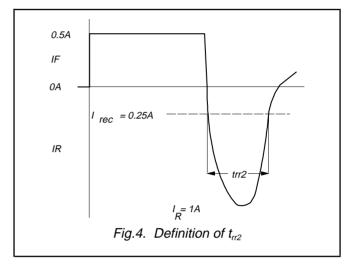
ELECTRICAL CHARACTERISTICS

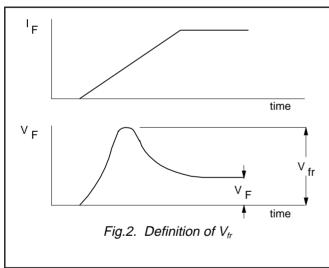
characteristics are per diode at T_i = 25 °C unless otherwise stated

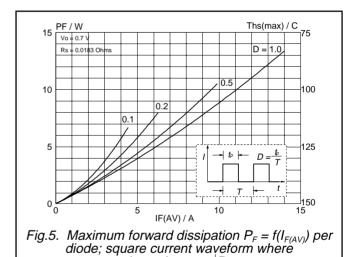
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------------|-------------------------------|--|------|------|------|------|
| V _F | Forward voltage | $I_F = 8 \text{ A}; T_i = 150^{\circ}\text{C}$ | 1 | 0.72 | 0.85 | V |
| | | $I_{\rm F} = 20 {\rm A}^{ \prime}$ | - | 1.00 | 1.15 | V |
| I _R | Reverse current | $\dot{V}_R = V_{RWM}$; $T_i = 100 ^{\circ}C$ | - | 0.2 | 0.6 | mΑ |
| | | $V_{R} = V_{RWM}$ | - | 6 | 30 | μΑ |
| Q_s | Reverse recovery charge | $I_{\rm F} = 2 \text{ A}; V_{\rm R} \ge 30 \text{ V}; -dI_{\rm F}/dt = 20 \text{ A/}\mu\text{s}$ | - | 8 | 12.5 | nC |
| t _{rr1} | Reverse recovery time | $I_{F} = 1 \text{ A}; V_{R} \ge 30 \text{ V};$ | - | 20 | 25 | ns |
| | 1 | -dl ₌ /dt = 100 A/μs | | | | |
| t _{rr2} | Reverse recovery time | $I_{\rm F} = 0.5 \text{A} \text{ to } I_{\rm R} = 1 \text{A}; I_{\rm rec} = 0.25 \text{A}$ | - | 10 | 20 | ns |
| I I'rm | Peak reverse recovery current | $I_{\rm F} = 1 \text{ A}; V_{\rm R} \ge 30 \text{ V};$ | - | 1.5 | 2 | Α |
| l | ĺ | $-dI_{\rm F}/dt = 50$ A/ μ s; $T_{\rm i} = 100$ °C | | | | |
| V_{fr} | Forward recovery voltage | $I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}$ | - | 1 | - | V |

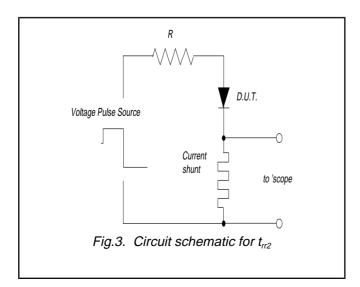
BYV32F, BYV32EX series

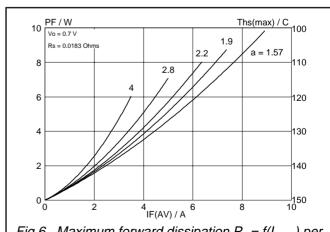








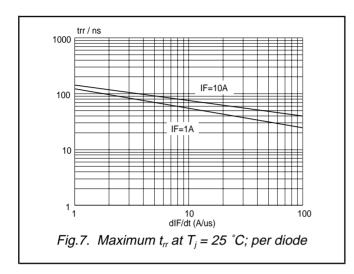


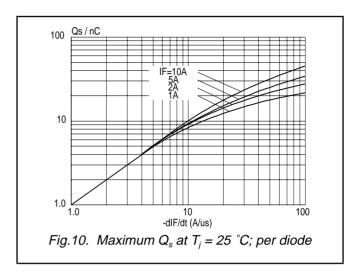


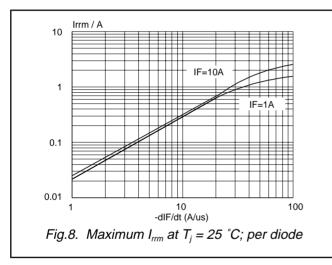
 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

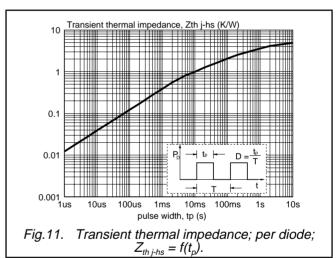
Fig.6. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.

BYV32F, BYV32EX series









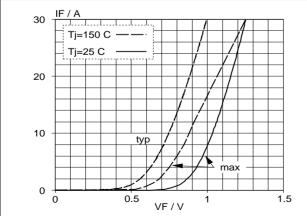
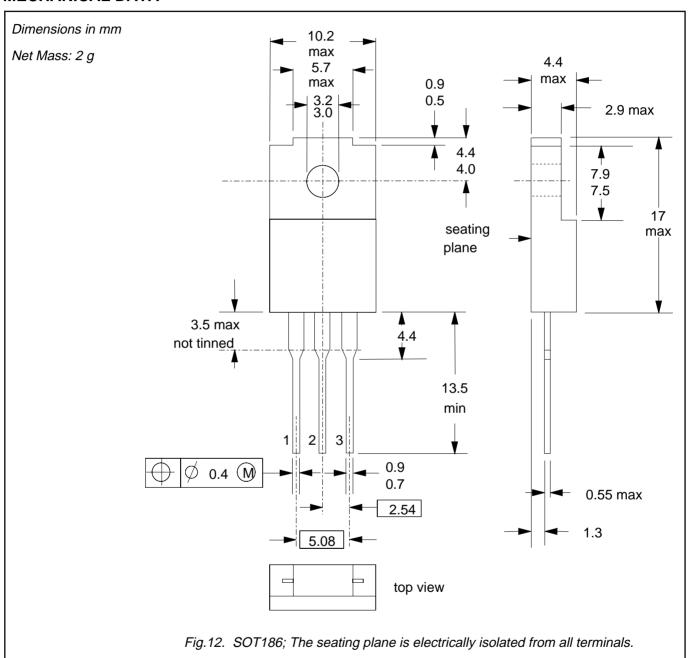


Fig.9. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

BYV32F, BYV32EX series

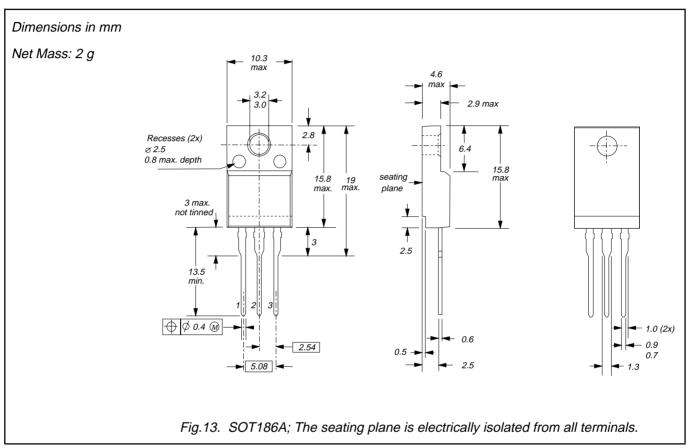
MECHANICAL DATA



- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

BYV32F, BYV32EX series

MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes ultrafast, rugged

BYV32F, BYV32EX series

DEFINITIONS

| Data sheet status | | | | |
|---|---|--|--|--|
| Objective specification This data sheet contains target or goal specifications for product development. | | | | |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. | | | |
| Product specification | This data sheet contains final product specifications. | | | |
| Limiting values | | | | |

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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